

Amendments to the Specification:

Please replace the Title, all occurrences, with the following amended Title:

~~OPTIMIZED~~ MONOLITHICALLY INTEGRATED TRENCH POWER MOSFET ~~WITH~~
~~INTEGRATED~~ AND SCHOTTKY DIODE

Please replace paragraph [0001] with the following amended paragraph:

[0001] The present invention relates in general to semiconductor power device technology, and in particular to a semiconductor power device with a monolithically integrated trench gate MOSFET and Schottky diode ~~integrated in an optimum manner~~, and its method of manufacture.